

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

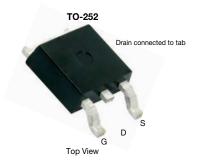
PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0150				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0190				
I _D (A)	30				
Configuration	Single				
Package	TO-252				

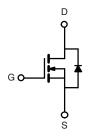
FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- \bullet 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V_{DS}	100	V		
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current	$T_C = 25$ °C ^a	1	30			
	T _C = 125 °C	l _D	27			
Continuous Source Current (Diode Conduction	I _S	30	Α			
Pulsed Drain Current ^b	I _{DM}	120				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	34			
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	58	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	71	W		
	T _C = 125 °C		23	V V		
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)		R_{thJC}	2.1	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	,							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		-	2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	250	-	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0120	0.0150	Ω	
Dynin Course On Ctota Basistanas 3	Б	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0255		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0320		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0145	0.0190		
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 25 A		-	58	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	1565	2100		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	800	1100	pF		
Reverse Transfer Capacitance	C _{rss}			-	65	100		
Total Gate Charge ^c	Qg			-	26.5	40		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 30 \text{ A}$	-	5.5	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	5.5	-		
Gate Resistance	R_g	f = 1 MHz		1.1	2.3	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}				7	15		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 1.67 \Omega$ $I_{D} \cong 30 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	19	30	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	18	30		
Fall Time ^c	t _f			-	59	95		
Source-Drain Diode Ratings and Chara	acteristics b							
Pulsed Current ^a	I _{SM}			-	-	120	Α	
Forward Voltage	V_{SD}	I _F = 30 A, V _{GS} = 0 V			0.94	1.5	V	

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

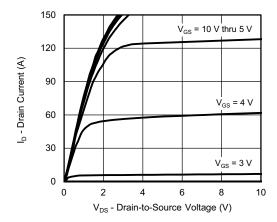
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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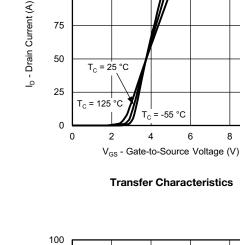
8



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics



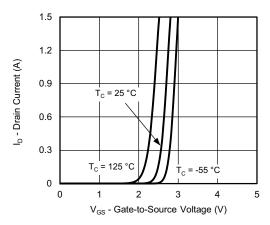
125

100

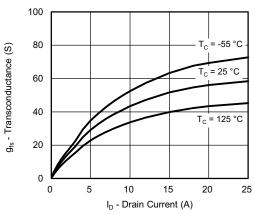
75



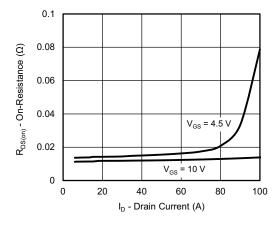
6



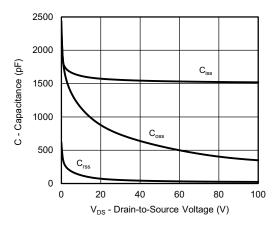
Transfer Characteristics



Transconductance



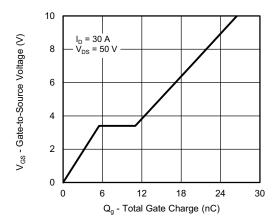
On-Resistance vs. Drain Current



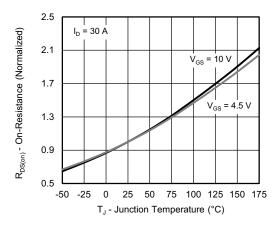
Capacitance



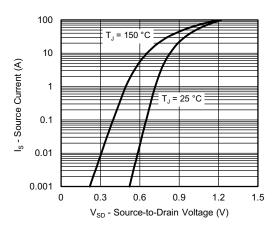
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



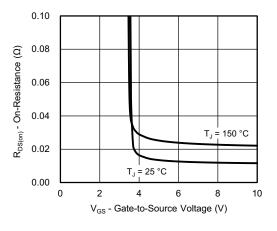
Gate Charge



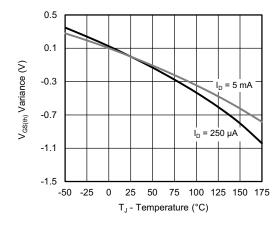
On-Resistance vs. Junction Temperature



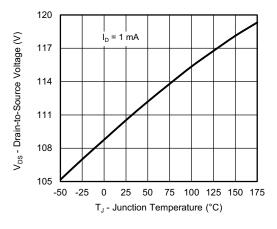
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



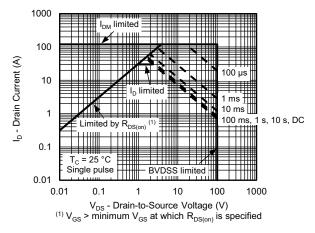
Threshold Voltage



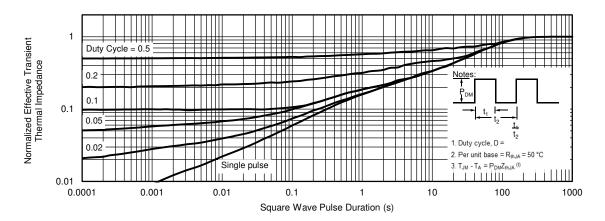
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



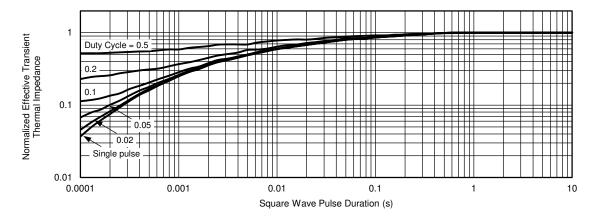
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

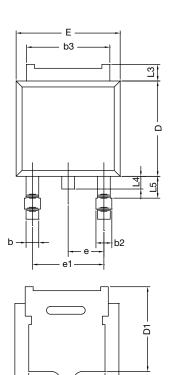
- Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

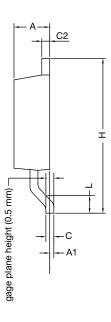
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg278633.



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TO-252AA Case Outline





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56 BSC		0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

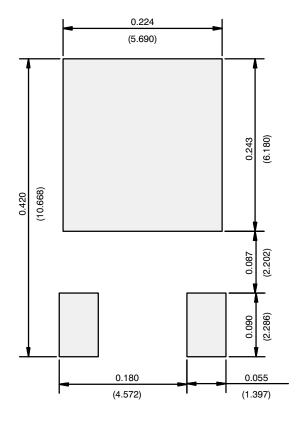
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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